

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

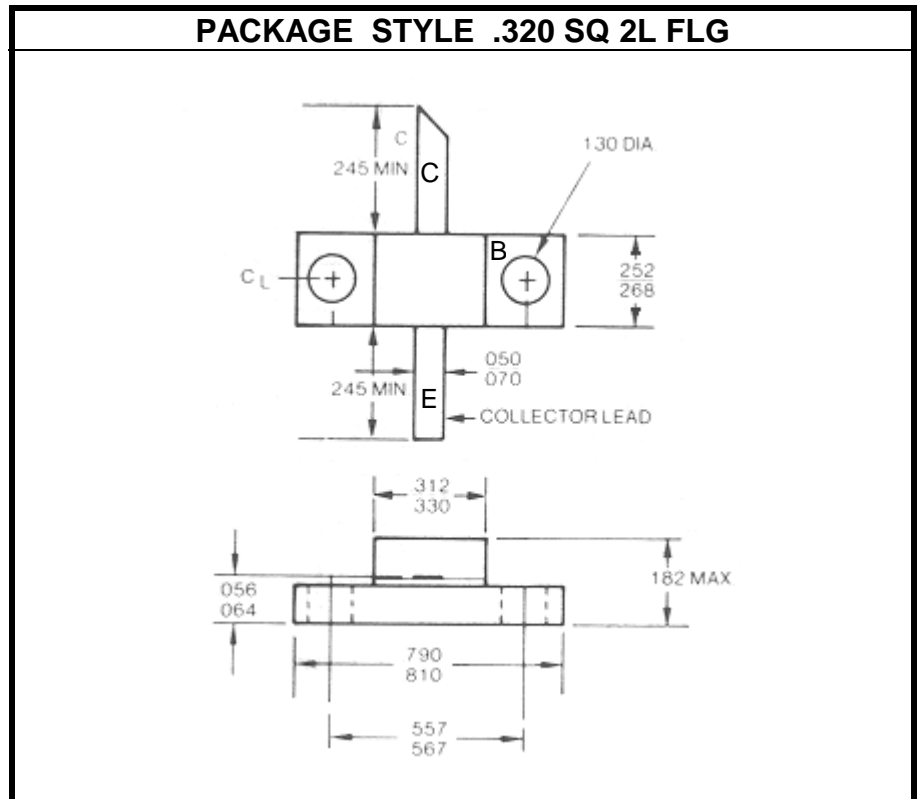
The **ASI MRA1014-35** is Designed for Class C, Common Base Wideband Large Signal Amplifier Applications From 1.0 GHz to 1.4 GHz.

FEATURES:

- Diffused Ballast Resistors.
- Internal Matching Network
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A (CONT)
V_{CES}	50 V
V_{EBO}	3.5 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.5 °C/W


CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 200 mA	50			V
BV_{EBO}	I _E = 2.5 mA	3.5			V
I_{CBO}	V _{CB} = 28 V			5.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	10		100	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz			24	pF
G_{PB}	V _{CE} = 28 V P _{out} = 35 W f = 1.0 GHz & 1.4 GHz	7.0			dB
η_C		50			%